

P-Channel Enhancement Mode MOSFET

Electrical Characteristics (TA=25°C Unless Otherwise Noted)

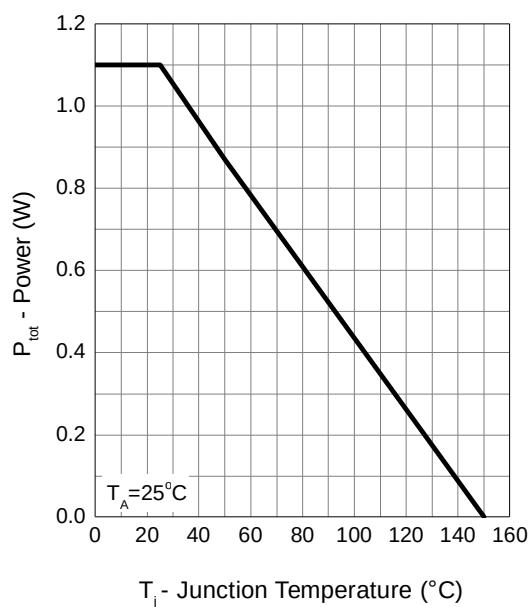
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-32V, V _{GS} =0V	-	-	-1	μA
		T _J =85°C	-	-	-30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.0	-1.4	-2.0	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-5.5A	-	35	50	mΩ
		V _{GS} =-4.5V, I _{DS} =-3A	-	48	55	
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V	-	-0.8	-1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =-3A, dI _{SD} /dt=100A/μs	-	18	-	ns
Q _{rr}	Reverse Recovery Charge		-	11	-	nC
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-20V, Frequency=1.0MHz	-	360	-	pF
C _{oss}	Output Capacitance		-	58	-	
C _{rss}	Reverse Transfer Capacitance		-	40	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-20V, R _L =20Ω, I _{DS} =-1A, V _{GEN} =-10V, R _G =6Ω	-	8	-	ns
t _r	Turn-on Rise Time		-	6	-	
t _{d(OFF)}	Turn-off Delay Time		-	25	-	
t _f	Turn-off Fall Time		-	14	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =-20V, V _{GS} =-10V, I _{DS} =-3A	-	8.3	-	nC
Q _{gs}	Gate-Source Charge		-	1.7	-	
Q _{gd}	Gate-Drain Charge		-	1.9	-	

Note a : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

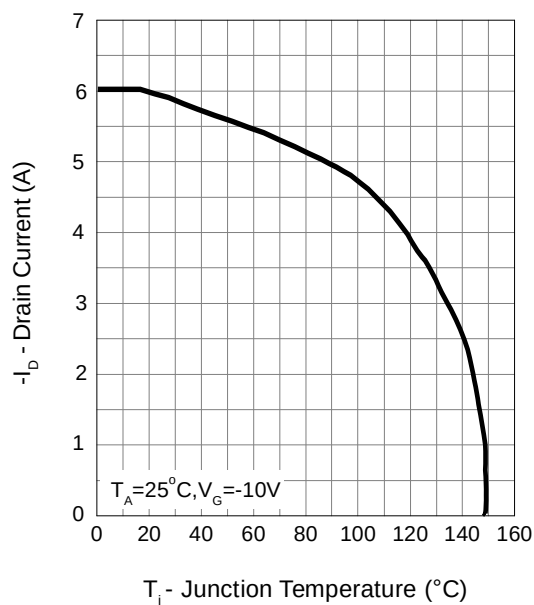
Note b : Guaranteed by design, not subject to production testing.

Typical Performance Characteristics (TA=25°C unless otherwise Specified)

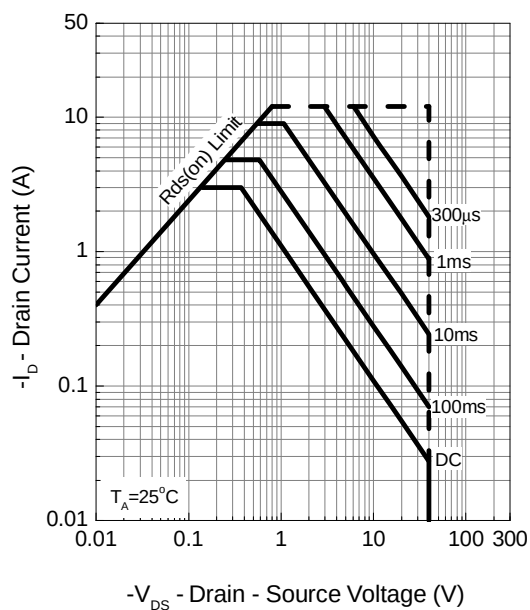
Power Dissipation



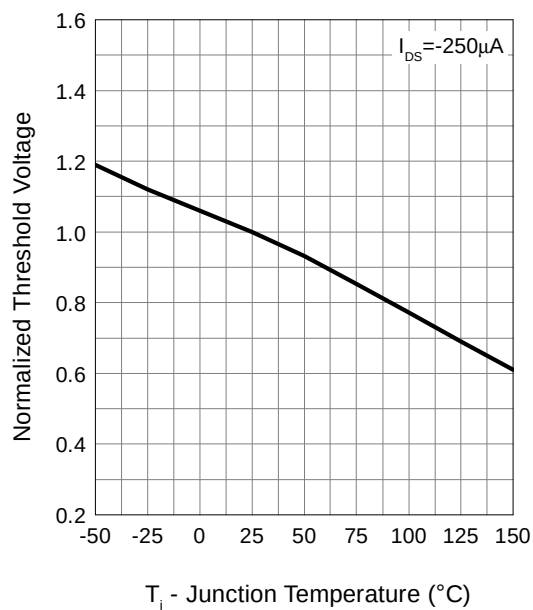
Drain Current



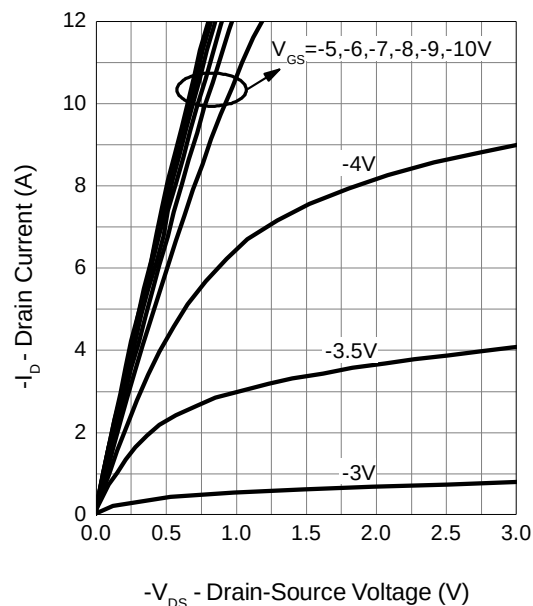
Safe Operation Area



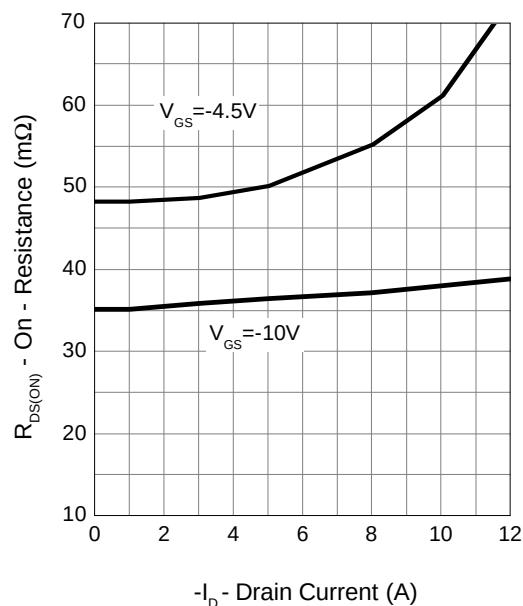
Gate Threshold Voltage



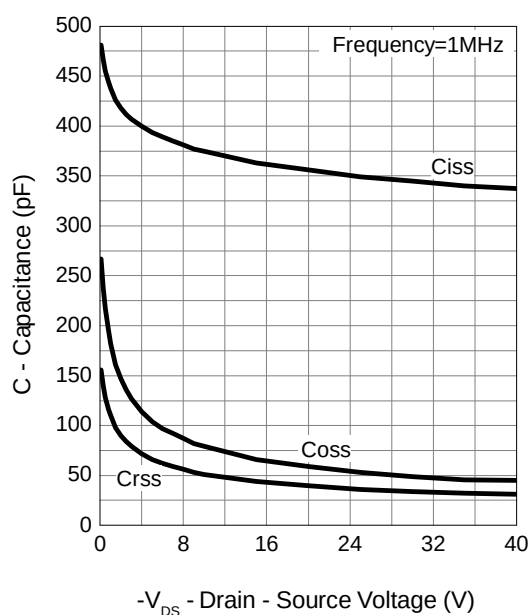
Output Characteristics



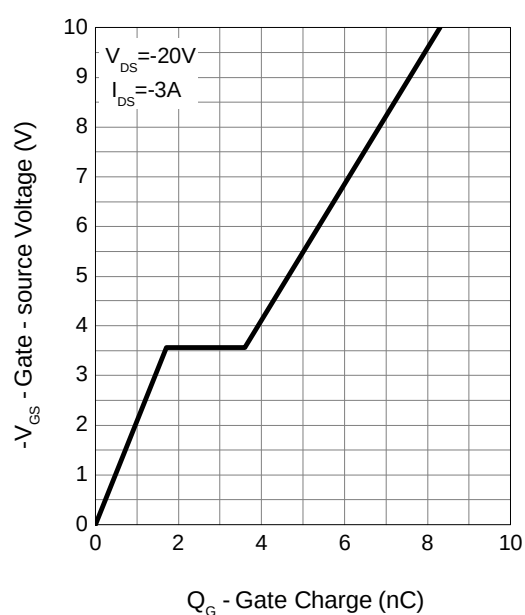
Drain-Source On Resistance



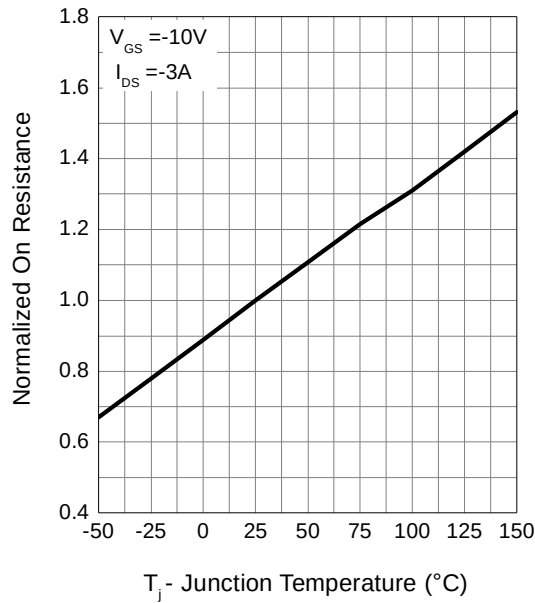
Capacitance



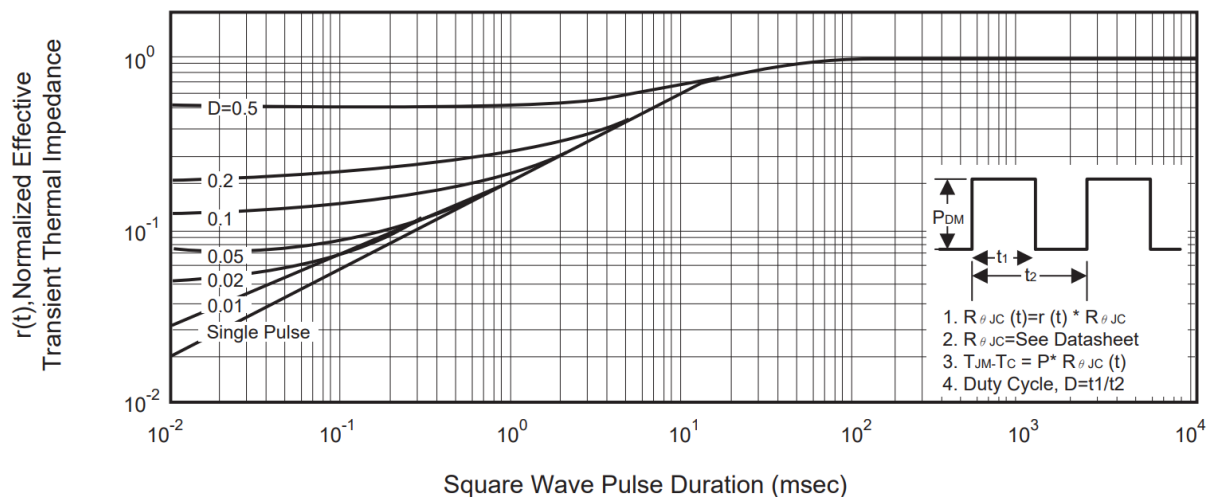
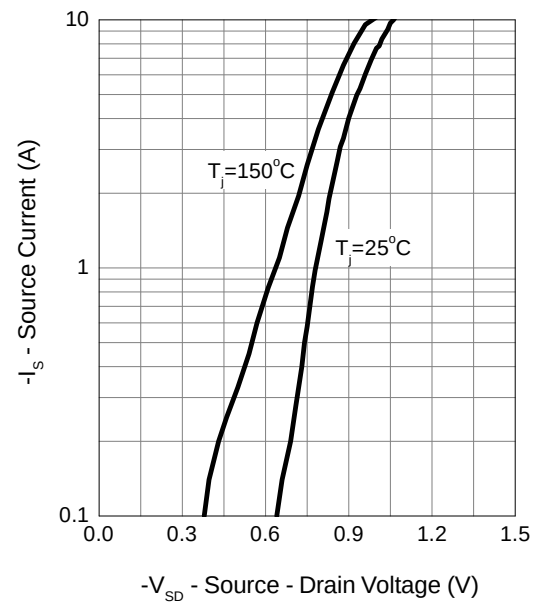
Gate Charge



Drain-Source On Resistance

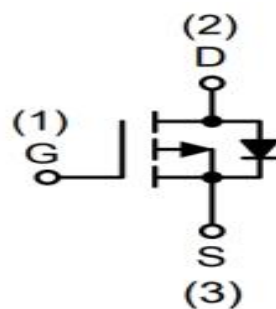
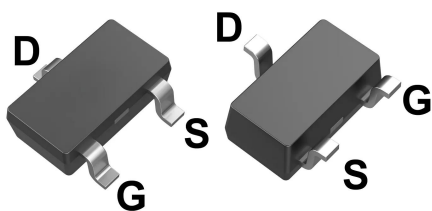


Source-Drain Diode Forward

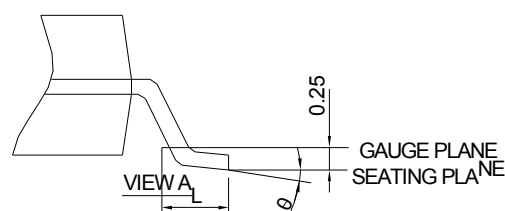
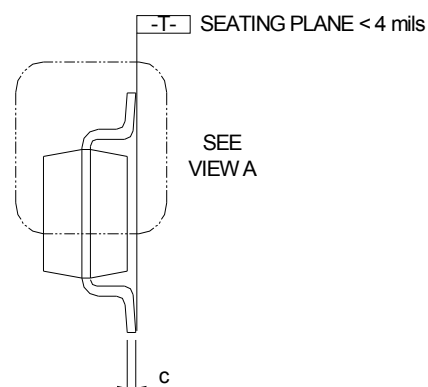
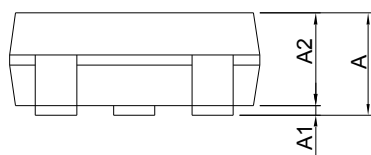
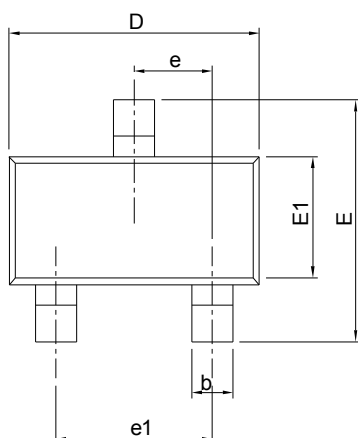


PACKAGE OUTLINE DIMENSIONS

SOT23-3L Pin Configuration



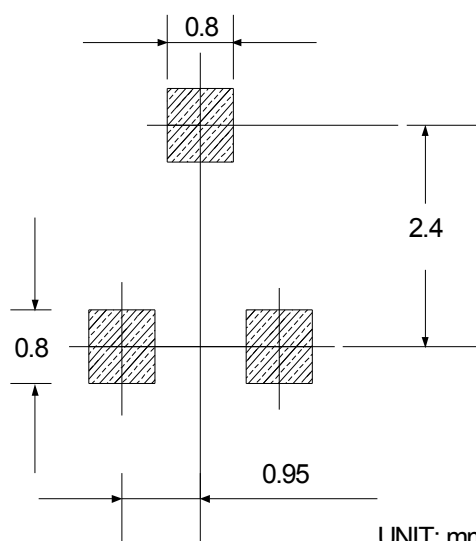
Schematic Diagram



SYMBOL	SOT23-3L			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	-	1.20	-	0.047
A1	0.00	0.08	0.000	0.003
A2	0.90	1.12	0.035	0.044
b	0.30	0.50	0.012	0.020
c	0.08	0.22	0.003	0.009
D	2.70	3.10	0.106	0.122
E	2.60	3.00	0.102	0.118
E1	1.40	1.80	0.055	0.071
e	0.95 BSC		0.037 BSC	
e1	1.90 BSC		0.075 BSC	
L	0.30	0.60	0.012	0.024
θ	0°	8°	0°	8°

Note : Dimension D and E1 do not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 10 mil per side.

RECOMMENDED LAND PATTERN



UNIT: mm